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H. C. Chan

4/16/05

Date

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: Hyun-Jin Cho, et al.	)	Examiner: Tran, Mai Huong C
	)	
Serial No.: 10/666,220	)	Group Art Unit: 2818
	)	
Filed: September 19, 2003	)	
	)	
For: Stability in Thyristor-Based Memory Device	)	
	)	

**SUBMISSION OF DOCUMENTS REQUESTED BY EXAMINER**

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In the Office Action dated March 28, 2005, the Examiner requested the submission of copies of three documents. Enclosed are the requested documents. Also enclosed is a copy of a previous submitted PTO-1449 listing these references. Please initial the PTO-1449 after considering the references.

The Commissioner is authorized to charge any fees in this submission to deposit account 50-2538 (docket number C002-D-2)

Date: April 16, 2005

Respectfully submitted,

Hark C. Chan  
Hark C. Chan (Reg. No. 35,477)



PTO/SB/08B (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449/PTO

**Complete if Known**

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 2

of 2

**Application Number** 10/666,220

**Filing Date** 9/19/2003

**First Named Inventor** Cho

**Art Unit** 2818

**Examiner Name** Tran, Mai Huong C

**Attorney Docket Number** C002-D-2

### NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		Nemati, Farid and Plummer, James, D., A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device, VLSI Technology Technical Digest, 6/1998	
		Nemati, Farid and Plummer, James, D., A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories, International Electron Device Meeting Technical Digest, 1999	
		Gribnikov, Z.S., Korobov, V.A., and Mitin, V.V., The Tunnel Diode as a Thyristor Emitter, Solid-State Electronics, Vol. 42, No. 9, 1998, pp. 1761-1763	

Examiner Signature	Date Considered
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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